

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-43 (Canceled)

44. (Currently Amended) An active matrix type display device comprising:

a substrate;

a pixel circuit formed over said substrate for switching pixels of said display device;

a resin formed on said substrate;

a base film ~~in contact with~~ on said resin;

a driver circuit comprising thin film transistors on said base film, wherein said base film is formed between said resin and said driver circuit, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;

a passivation film covering said driver circuit, said passivation film having a contact hole to allow an electrical connection between at least one of said thin film transistors and said pixel circuit;

a wiring formed over said passivation film to form said electrical connection; and

a sealing member over said substrate, wherein said sealing member encloses said pixel circuit and said driver circuit.

45. (Previously Presented) An active matrix type display device according to claim 44 wherein said passivation film comprises at least two layers having different etching rates, and said contact hole has a tapered configuration.

46. (Previously Presented) An active matrix type display device according to claim 44 wherein each of said thin film transistors has a channel region comprising crystalline silicon.
47. (Previously Presented) An active matrix type display device according to claim 44 wherein said substrate comprises a plastic.
48. (Previously Presented) An active matrix type display device according to claim 44 wherein said driver circuit is overlapped by another substrate opposed to said substrate.
49. (Canceled)
50. (Canceled)
51. (Previously Presented) An active matrix type display device according to claim 44 wherein said passivation film comprises polyimide.
52. (Previously Presented) An active matrix type display device according to claim 44 wherein said passivation film comprises silicon oxide.
53. (Previously Presented) An active matrix type display device according to claim 44 wherein said pixel circuit comprises a first plurality of transparent conductive films and a second plurality of transparent conductive films extending across said first plurality of transparent conductive films.
54. (Previously Presented) An active matrix type display device according to claim 44 wherein said pixel circuit comprises pixel electrodes connected to TFTs.
- 55-69. (Canceled)

70. (Previously Presented) An active matrix type display device according to claim 44 wherein said driver circuit is formed from a stick substrate separate from said substrate.

71. (Canceled)

72. (Currently Amended) An active matrix type display device comprising:  
a pixel circuit formed over a substrate for switching pixels of said display device;  
a resin formed on said substrate;  
a base film ~~in contact with~~ on said resin;  
a driver circuit comprising thin film transistors on said base film, wherein said base film is formed between said resin and said driver circuit, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;  
an insulating film formed over said driver circuit; and  
a wiring formed over said insulating film, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

73. (Original) An active matrix type display device according to claim 72 wherein each of said thin film transistors has a channel region comprising crystalline silicon.

74. (Original) An active matrix type display device according to claim 72 wherein said substrate comprises a plastic.

75. (Original) An active matrix type display device according to claim 72 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

76. (Original) An active matrix type display device according to claim 72 wherein said driver circuit is formed from a stick substrate separate from said substrate.

77. (Original) An active matrix type display device according to claim 72 wherein said display device is a liquid crystal display device.

78. (Currently Amended) An active matrix type display device comprising:  
a pixel circuit formed over a substrate for switching pixels of said display device;  
a resin formed on said substrate;  
a base film ~~in contact with~~ on said resin;  
a driver circuit comprising thin film transistors on said base film, wherein said base film is formed between said resin and said driver circuit, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;  
an insulating film formed over said driver circuit; and  
a wiring comprising indium tin oxide formed over said insulating film, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

79. (Original) An active matrix type display device according to claim 78 wherein each of said thin film transistors has a channel region comprising crystalline silicon.

80. (Original) An active matrix type display device according to claim 78 wherein said substrate comprises a plastic.

81. (Original) An active matrix type display device according to claim 78 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

82. (Original) An active matrix type display device according to claim 78 wherein said driver circuit is formed from a stick substrate separate from said substrate.

83. (Original) An active matrix type display device according to claim 78 wherein said display device is a liquid crystal display device.

84. (Currently Amended) An active matrix type display device comprising:  
a pixel circuit formed over a substrate for switching pixels of said display device;  
a resin formed on said substrate;  
a base film ~~in contact with~~ on said resin;  
a driver circuit comprising thin film transistors on said base film, wherein said base film is formed between said resin and said driver circuit, each of said thin film transistors comprising a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;  
an insulating film formed over said driver circuit; and  
a wiring comprising indium tin oxide formed over said insulating film and extending on a same layer as said resin, wherein said driver circuit is electrically connected to said pixel circuit through said wiring.

85. (Original) An active matrix type display device according to claim 84 wherein each of said thin film transistors has a channel region comprising crystalline silicon.

86. (Original) An active matrix type display device according to claim 84 wherein said substrate comprises a plastic.

87. (Original) An active matrix type display device according to claim 84 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

88. (Original) An active matrix type display device according to claim 84 wherein said driver circuit is formed from a stick substrate separate from said substrate.

89. (Original) An active matrix type display device according to claim 84 wherein said display device is a liquid crystal display device.

90. (Currently Amended) An active matrix type display device comprising:  
a pixel circuit formed over a substrate for switching pixels of said display device;  
a resin formed over said substrate;  
a base film ~~in contact with~~ on said resin;  
a semiconductor layer on said base film, wherein said base film is formed between said resin and said semiconductor layer;  
a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;  
at least one of source and drain electrodes electrically connected to said semiconductor layer;  
an insulating film formed over at least said semiconductor layer and said gate electrode;  
and  
a wiring formed over said insulating film, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.

91. (Original) An active matrix type display device according to claim 90 wherein said semiconductor layer comprises crystalline silicon.

92. (Original) An active matrix type display device according to claim 90 wherein said substrate comprises a plastic.

93. (Original) An active matrix type display device according to claim 90 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

94. (Original) An active matrix type display device according to claim 90 wherein said display device is a liquid crystal display device.

95. (Currently Amended) An active matrix type display device comprising:  
a pixel circuit formed over a substrate for switching pixels of said display device;  
a resin formed over said substrate;  
a base film ~~in contact with~~ on said resin;  
a semiconductor layer on said base film, wherein said base film is formed between said resin and said semiconductor layer;  
a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;  
at least one of source and drain electrodes electrically connected to said semiconductor layer;  
an insulating film formed over at least said semiconductor layer and said gate electrode;  
and  
a wiring comprising indium tin oxide formed over said insulating film, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.

96. (Original) An active matrix type display device according to claim 95 wherein said semiconductor layer comprises crystalline silicon.

97. (Original) An active matrix type display device according to claim 95 wherein said substrate comprises a plastic.

98. (Original) An active matrix type display device according to claim 95 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

99. (Original) An active matrix type display device according to claim 95 wherein said display device is a liquid crystal display device.

100. (Currently Amended) An active matrix type display device comprising:  
a pixel circuit formed over a substrate for switching pixels of said display device;  
a resin formed over said substrate;  
a base film ~~in contact with~~ on said resin;  
a semiconductor layer on said base film, wherein said base film is formed between said resin and said semiconductor layer;  
a gate electrode over said semiconductor layer with a gate insulating film interposed therebetween;  
at least one of source and drain electrodes electrically connected to said semiconductor layer;  
an insulating film formed over at least said semiconductor layer and said gate electrode;  
and  
a wiring comprising indium tin oxide formed over said insulating film and extending on a same layer as said resin, wherein said at least one of said source and drain electrodes is electrically connected to said pixel circuit through said wiring.

101. (Original) An active matrix type display device according to claim 100 wherein said semiconductor layer comprises crystalline silicon.

102. (Original) An active matrix type display device according to claim 100 wherein said substrate comprises a plastic.



Applicant : Shunpei Yamazaki, et al.  
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103. (Original) An active matrix type display device according to claim 100 wherein said insulating film comprises at least one selected from the group consisting of polyimide and silicon oxide.

104. (Original) An active matrix type display device according to claim 100 wherein said display device is a liquid crystal display device.